

**General Description:**

The LWT1H022H8 uses advanced SGT technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications. The package form is TO-220AB, which accords with the ROHS standard and Halogen Free standard.

**Features:**

- Fast Switching
- Low Gate Charge and  $R_{DS(ON)}$
- Low Reverse transfer capacitances

**Applications:**

- DC-DC Converter
- Portable Equipment
- Power Management

**100% DVDS Tested**

**100% Avalanche Tested**


**Package Marking and Ordering Information:**

Marking	Part Number	Package	Packing	Qty.
T1H022/LW H8/D.C.	LWT1H022H8	TO-220AB	Tube	50 Pcs

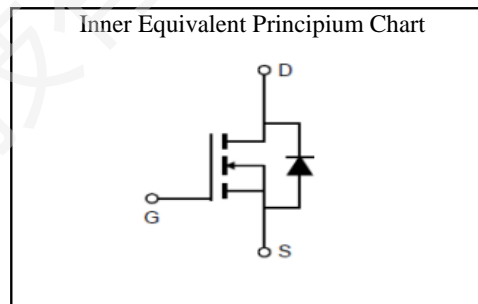
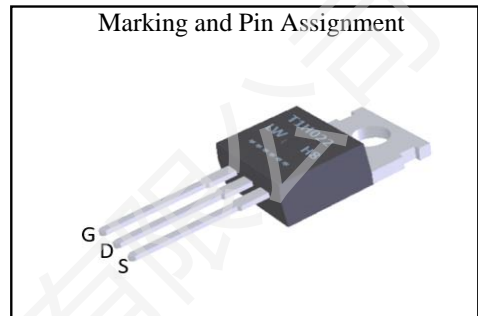
**Absolute Maximum Ratings:**

Symbol	Parameter	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	100	V
$I_D$	Continuous Drain Current	$T_C=25^\circ\text{C}$	200
	Continuous Drain Current	$T_C=100^\circ\text{C}$	127
$I_{DM}^{a1}$	Pulsed Drain Current	800	A
$E_{AS}^{a2}$	Single pulse avalanche energy	403	mJ
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$P_D$	Power Dissipation	227	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering	260	$^\circ\text{C}$

**Thermal Characteristics:**

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.55	$^\circ\text{C}/\text{W}$
$R_{\theta JA}^{a3}$	Thermal Resistance, Junction-to-Ambient	62	$^\circ\text{C}/\text{W}$

$V_{DSS}$	100	V
$I_D$	200	A
$P_D$	227	W
$R_{DS(ON) \text{ TYPE}}$	2.5	$\text{m}\Omega$



**Electrical Characteristic** ( $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$V_{DSS}$	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	--	--	V
$I_{DSS}$	Drain to Source Leakage Current	$V_{DS}=100V, V_{GS}=0V$	--	--	1.0	$\mu A$
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	3.0	3.5	4.0	V
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=20A$	--	2.5	3.2	$m\Omega$

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	--	6106	--	pF
$C_{oss}$	Output Capacitance	$V_{DS}=50V$	--	1804	--	
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0MHz$	--	23.4	--	
$R_G$	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	--	2.5	--	$\Omega$

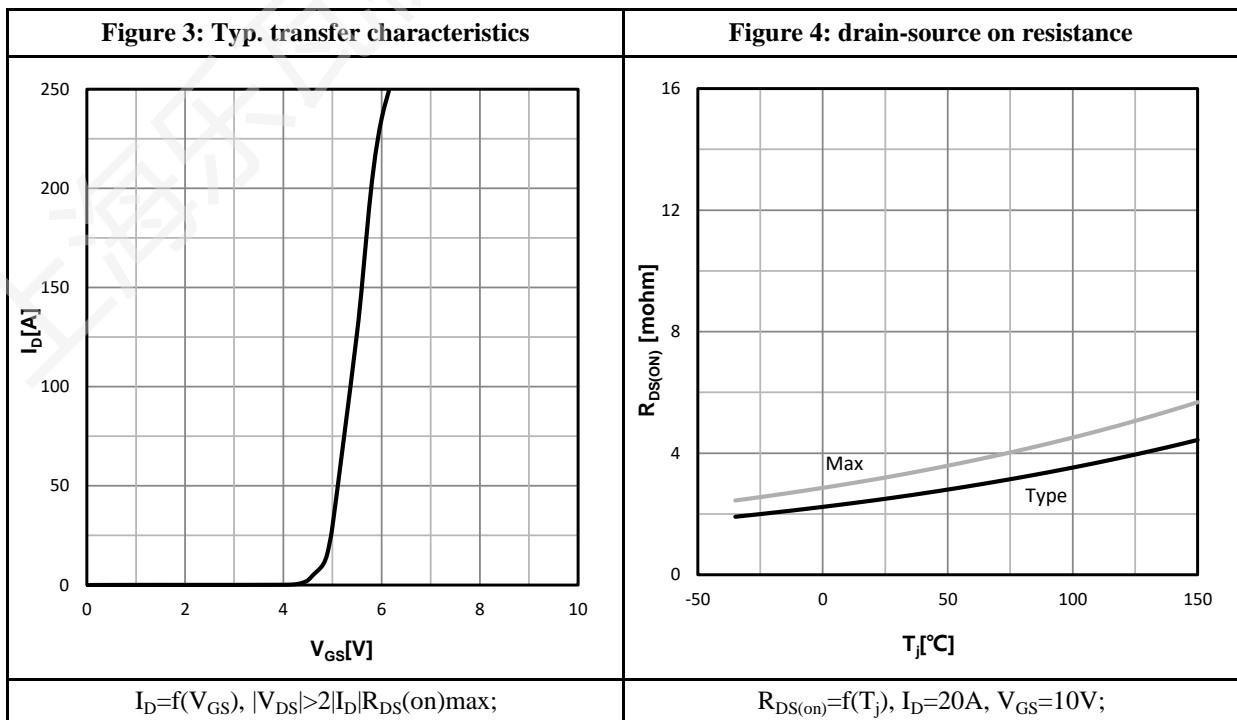
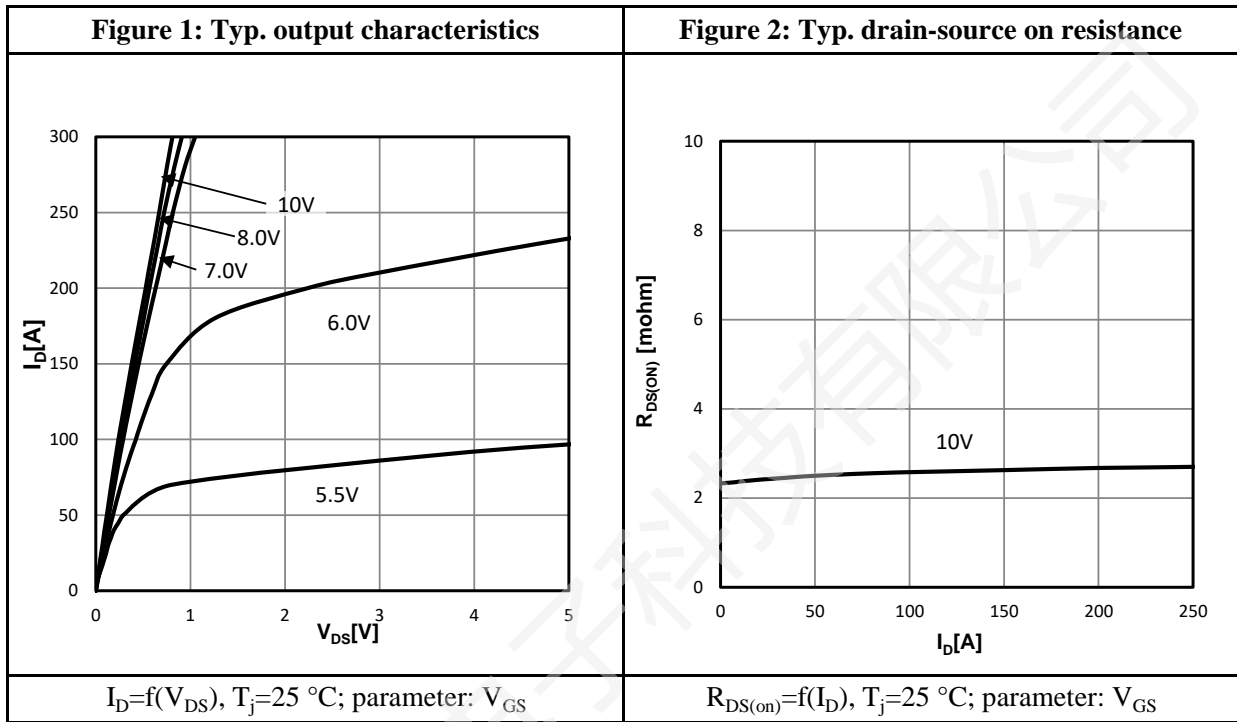
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=20A$	--	48	--	ns
$t_r$	Rise Time	$V_{DS}=50V$	--	56	--	
$t_{d(OFF)}$	Turn-Off Delay Time	$V_{GS}=10V$	--	75	--	
$t_f$	Fall Time	$R_G=3.0\Omega$	--	33	--	
$Q_g$	Total Gate Charge	$V_{GS}=10V$	--	81	--	nC
$Q_{gs}$	Gate Source Charge	$V_{DS}=50V$	--	28.9	--	
$Q_{gd}$	Gate Drain Charge	$I_D=20A$	--	14.7	--	

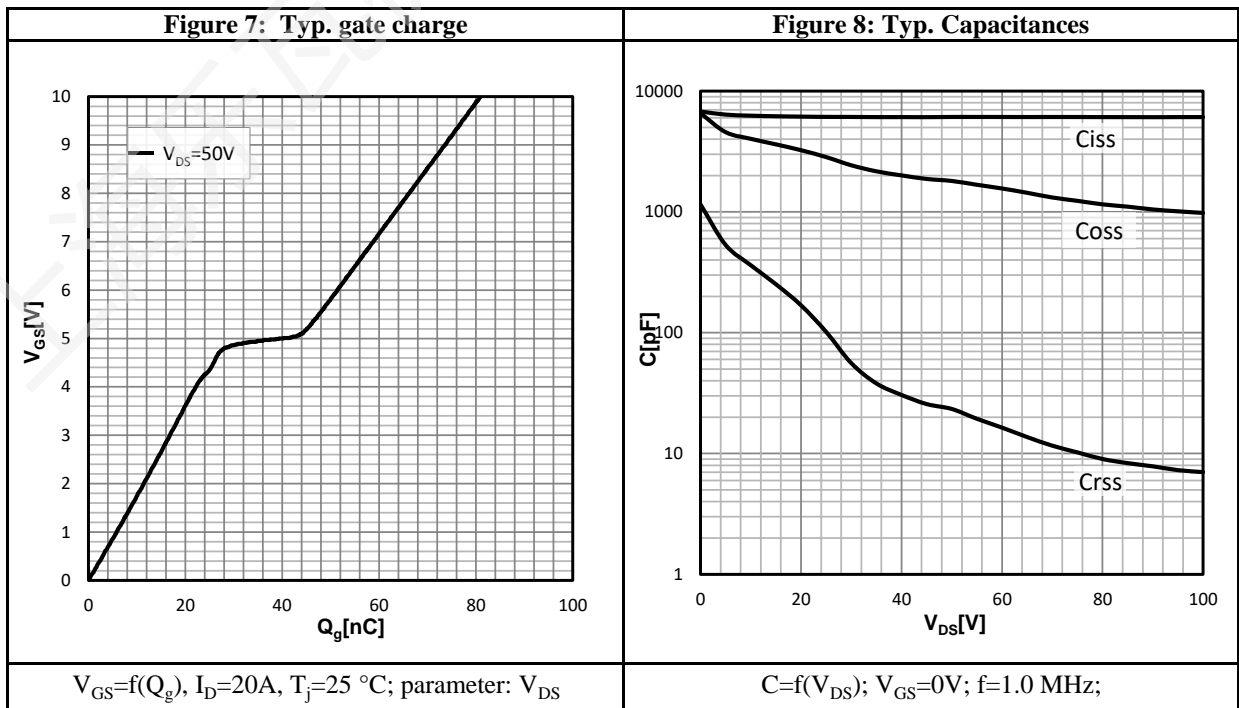
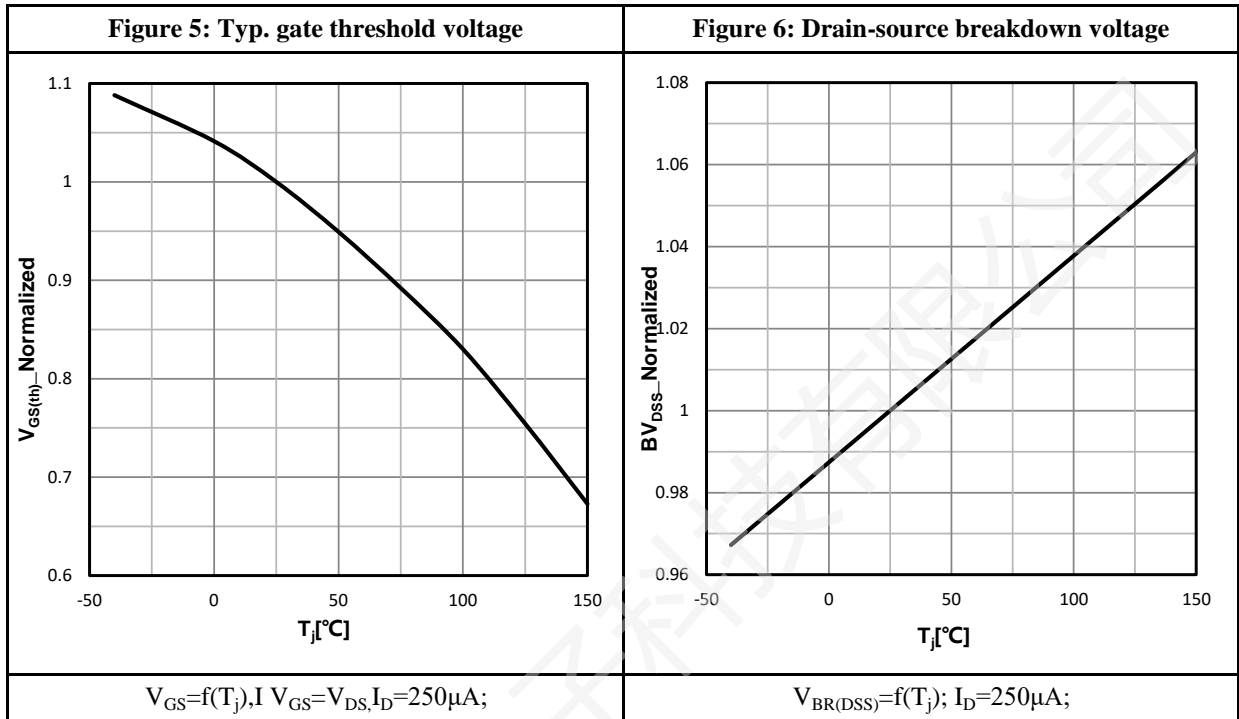
Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$I_S$	Diode Forward Current	$T_C=25\text{ }^\circ\text{C}$	--	--	200	A
$V_{SD}$	Diode Forward Voltage	$I_S=20A, V_{GS}=0V$	--	--	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_S=20A, V_{DD}=50V$	--	100	--	ns
$Q_{rr}$	Reverse Recovery Charge	$dI/dt=100A/\mu s$	--	467	--	nC

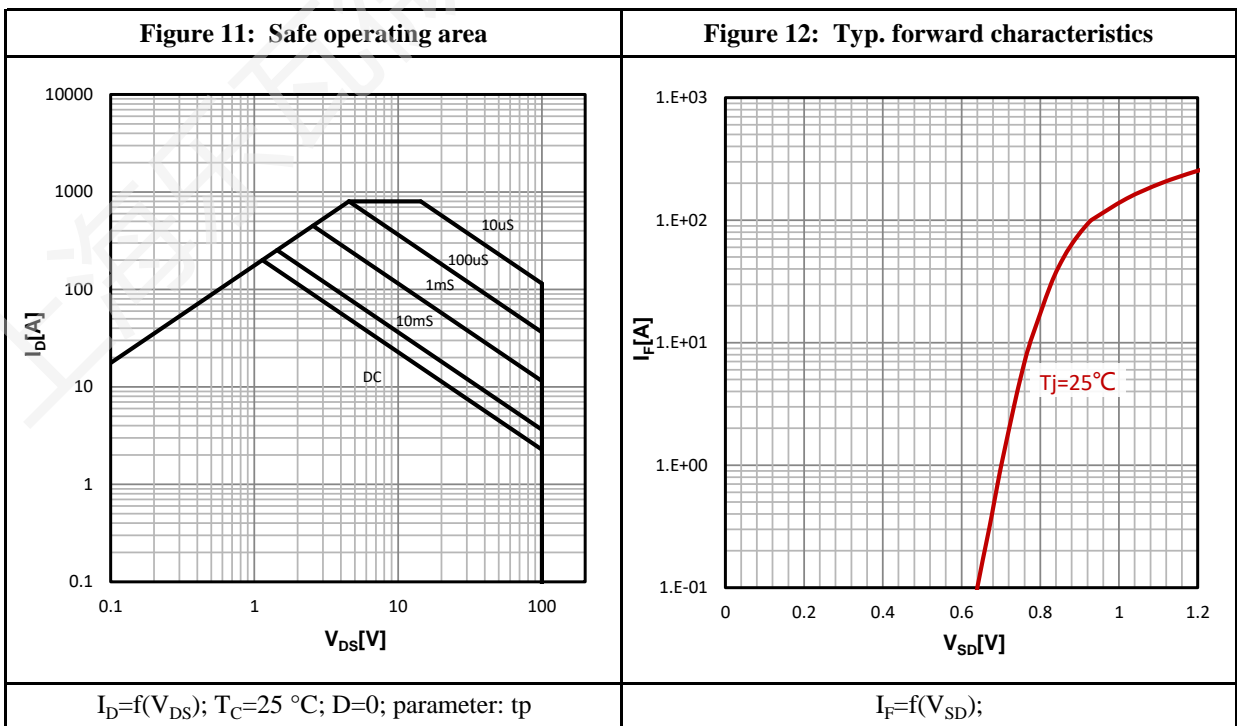
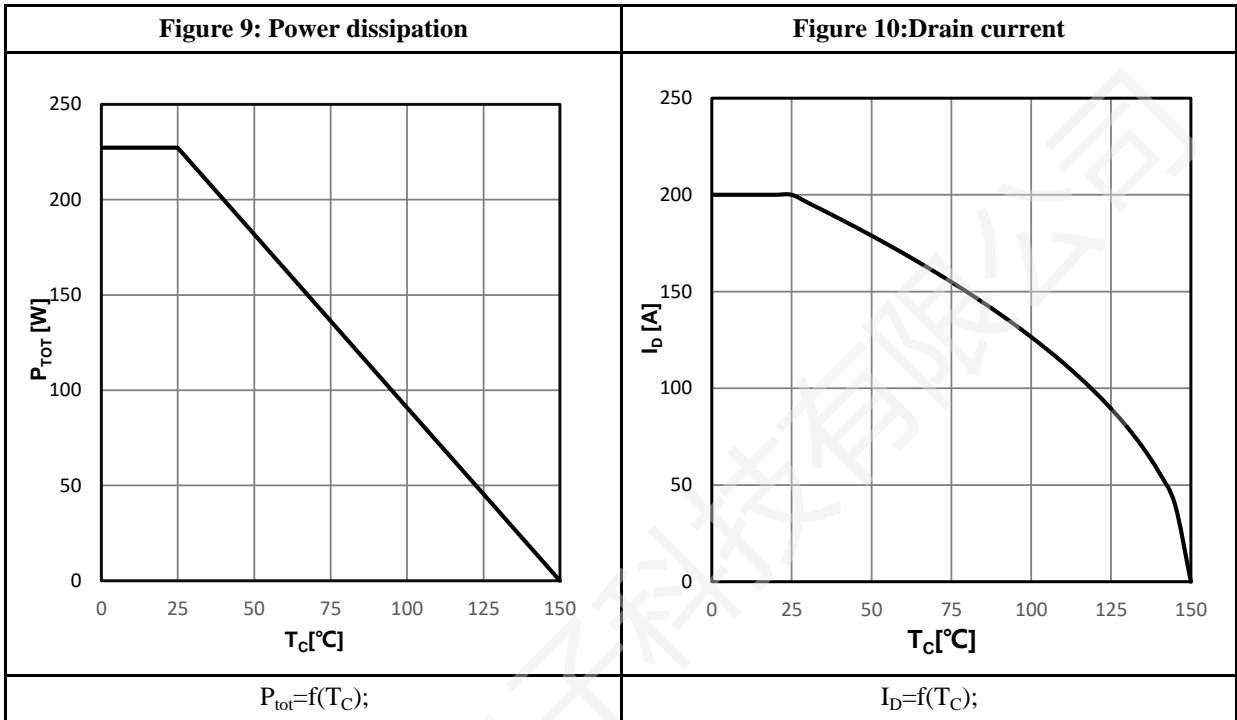
a1: Repetitive rating; pulse width limited by maximum junction temperature

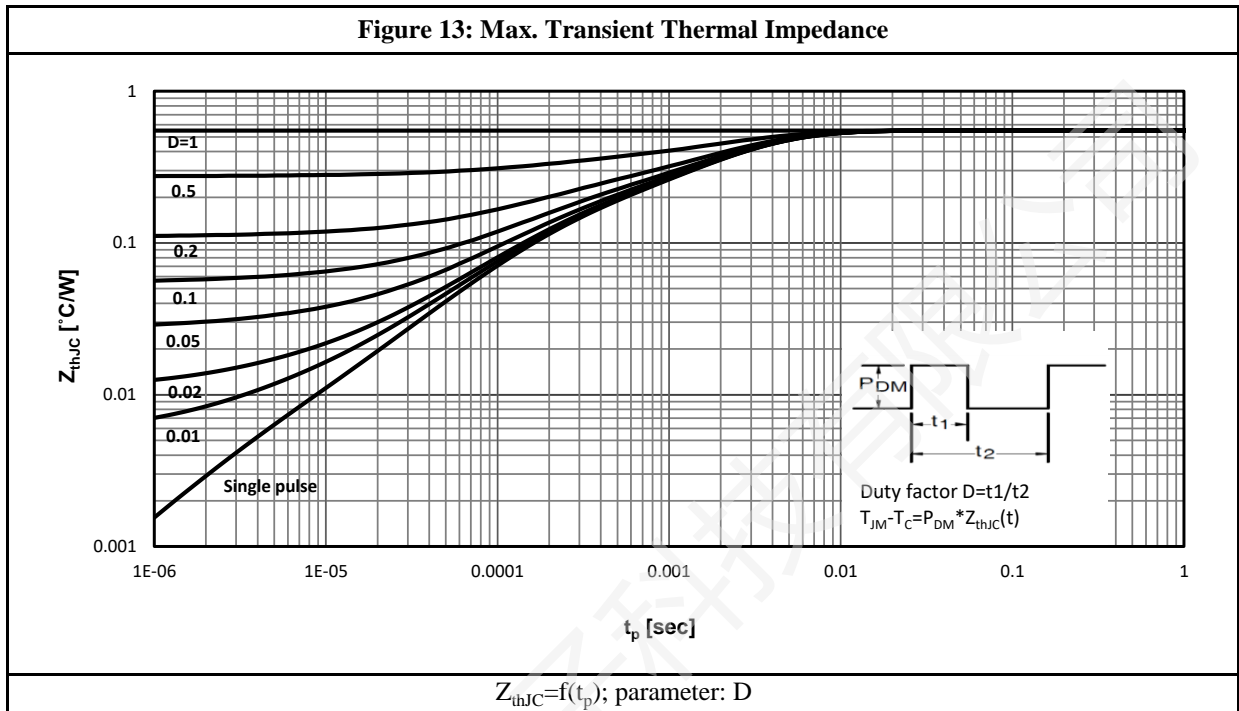
a2:  $V_{DD}=50V, L=0.1mH, R_G=25\Omega$ , Starting  $T_J=25\text{ }^\circ\text{C}$

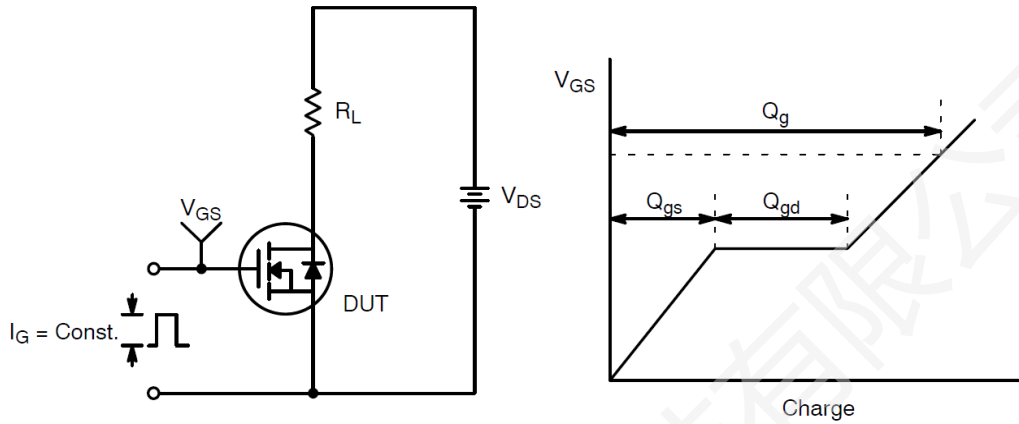
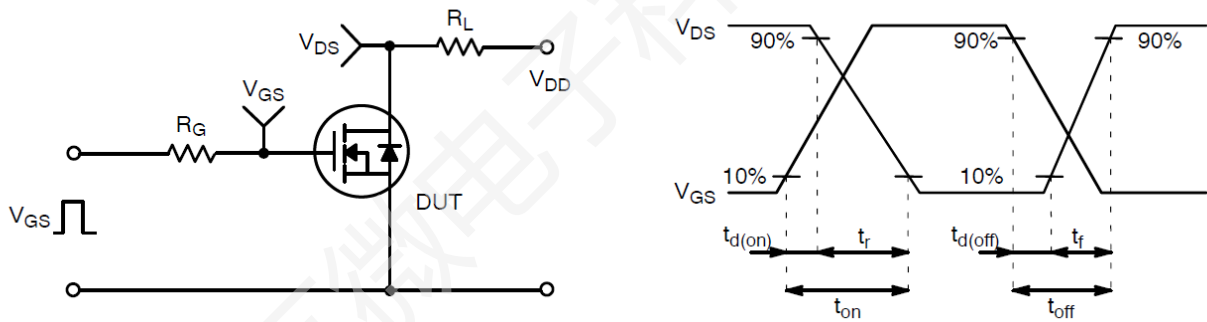
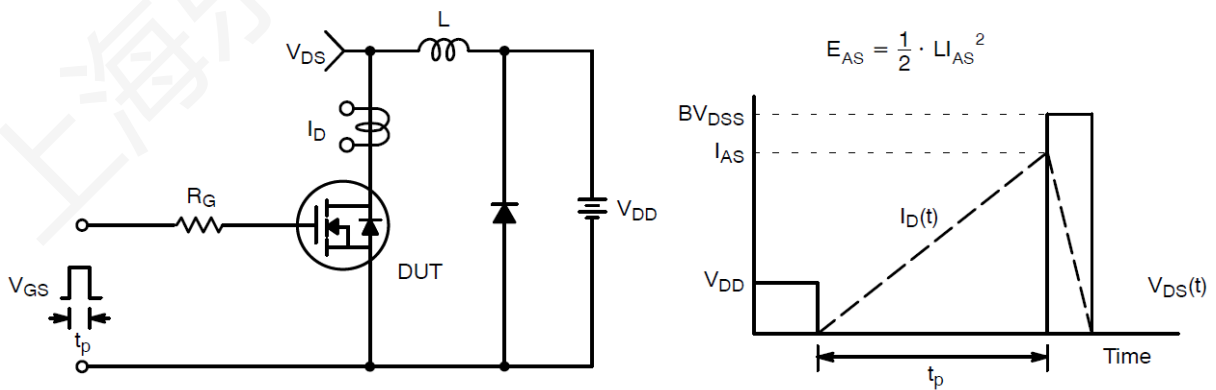
a3: Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu m$  thick) copper area for drain connection.

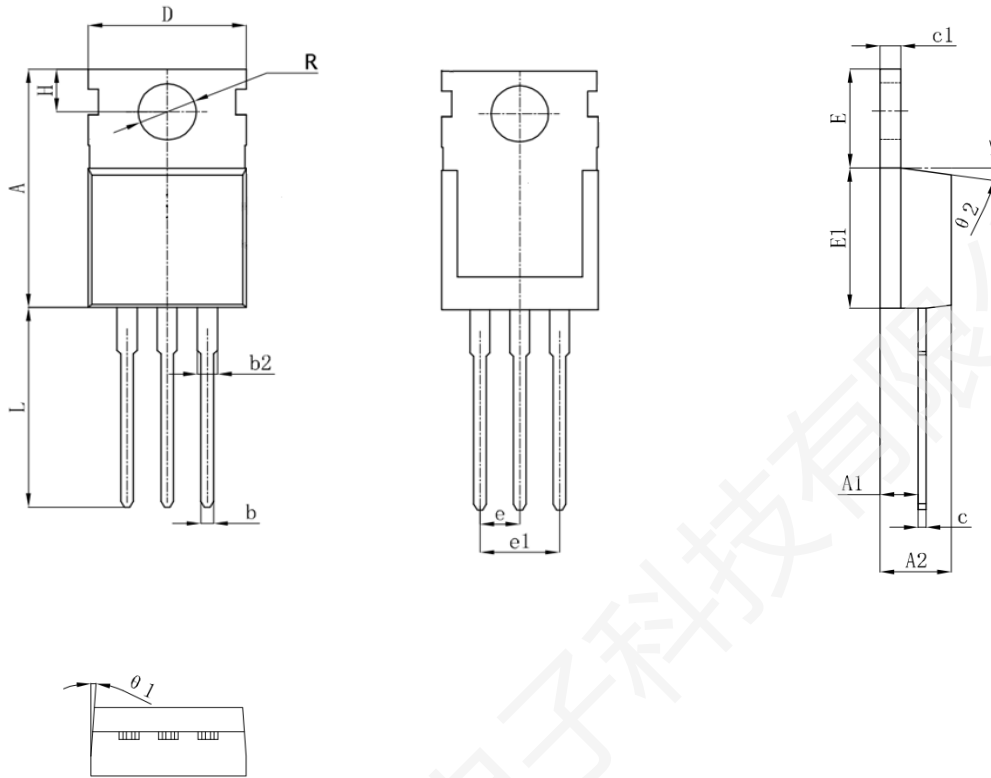
**Characteristics Curve:**








**Test Circuit & Waveform:**

**Figure 14: Gate Charge Test Circuit & Waveform**

**Figure 15: Resistive Switching Test Circuit & Waveforms**

**Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms**

**Package Outline:**


SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	15.3	15.55	15.8
A1	2.3	2.4	2.5
A2	4.4	4.5	4.7
b	0.7	0.8	0.9
b2	1.18	1.31	1.44
c	0.44	0.5	0.56
c1	1.28	1.3	1.33
D	9.8	10	12.2
E	6.4	6.5	6.6
E1	8.9	9.05	9.2
e	2.42	2.54	2.66
e1	4.84	5.08	5.32
H	2.73	2.8	2.87
H1	2.4	2.5	2.6
L	13.02	13.42	13.82
R	3.5	3.6	3.63
θ1	2°	2.5°	3°
θ2	6.5°	7°	7.5°

**Revision History:**

<b>Revison</b>	<b>Date</b>	<b>Descriptions</b>
Rev 1.0	May.2025	Initial Version

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